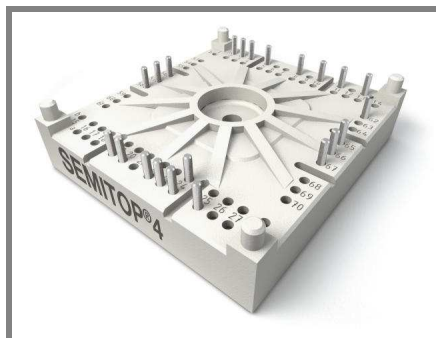


SK100GD126T



SEMITOP® 4

IGBT Module

SK100GD126T

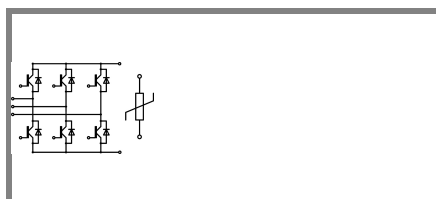
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 50 kVA
- Typ. motor power 22 kW

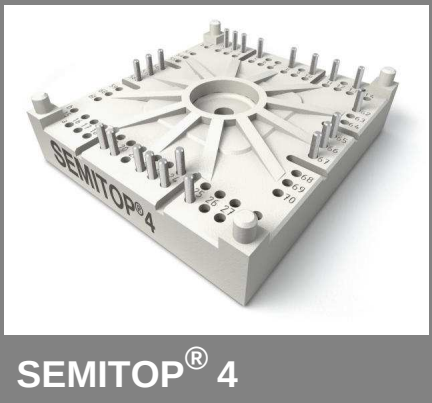


GD-T

Absolute Maximum Ratings				$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25\text{ °C}$			1200	V
I_C	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$		114	A
		$T_s = 70\text{ °C}$		86	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$			200	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 600\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 1200\text{ V}$			10	μs
Inverse Diode					
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$		118	A
		$T_s = 70\text{ °C}$		88	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$			200	A
Module					
$I_{t(RMS)}$					A
T_{vj}				-40 ... +150	$^{\circ}\text{C}$
T_{stg}				-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.			2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 4 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _J = 25 °C T _J = 125 °C			0,014	mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _J = 25 °C T _J = 125 °C			1200	nA nA
V _{CE0}		T _J = 25 °C T _J = 125 °C		1 0,9	1,2 1,1	V V
r _{CE}	V _{GE} = 15 V	T _J = 25°C T _J = 125°C		7 11	9,5 14	mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 100 A, V _{GE} = 15 V	T _J = 25°C _{chiplev.} T _J = 125°C _{chiplev.}		1,7 2,1	2,15 2,45	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz		7,2 0,37 0,32		nF nF nF
t _{d(on)} t _r E _{on}	R _{Gon} = 4 Ω di/dt = 2250 A/μs	V _{CC} = 600V I _C = 100A		115 28 9,8		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 4 Ω di/dt = 2250 A/μs	T _J = 125 °C V _{GE} = -7/+15 V		509 100 11,7		ns ns mJ
R _{th(j-s)}	per IGBT			0,4		K/W

SK100GD126T



IGBT Module

SK100GD126T

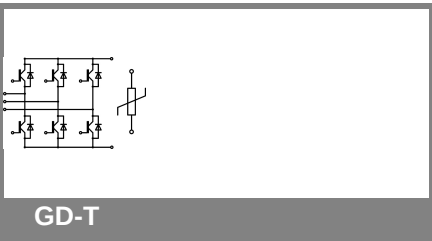
Preliminary Data

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- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

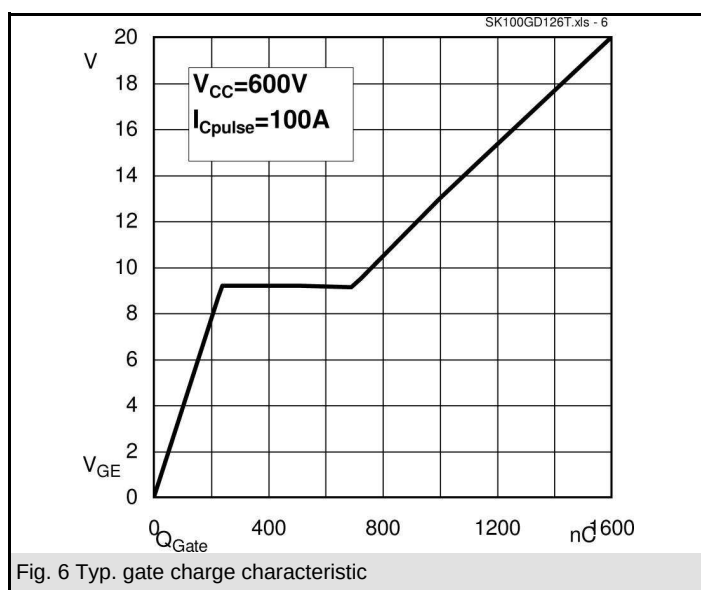
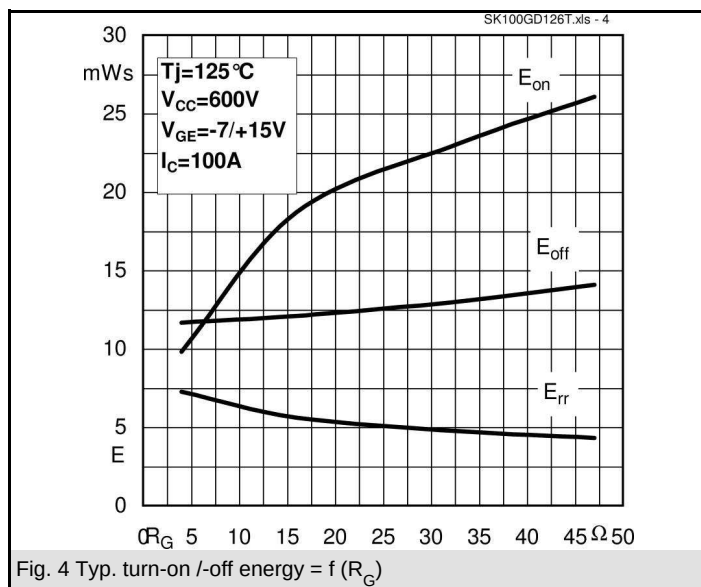
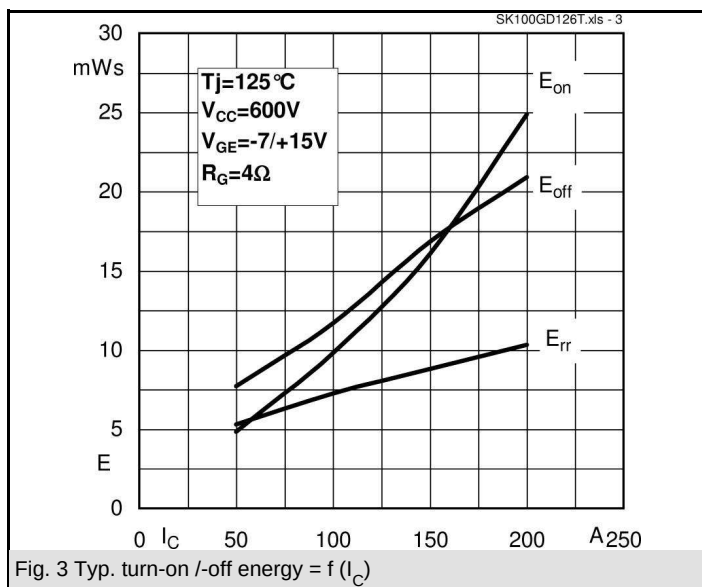
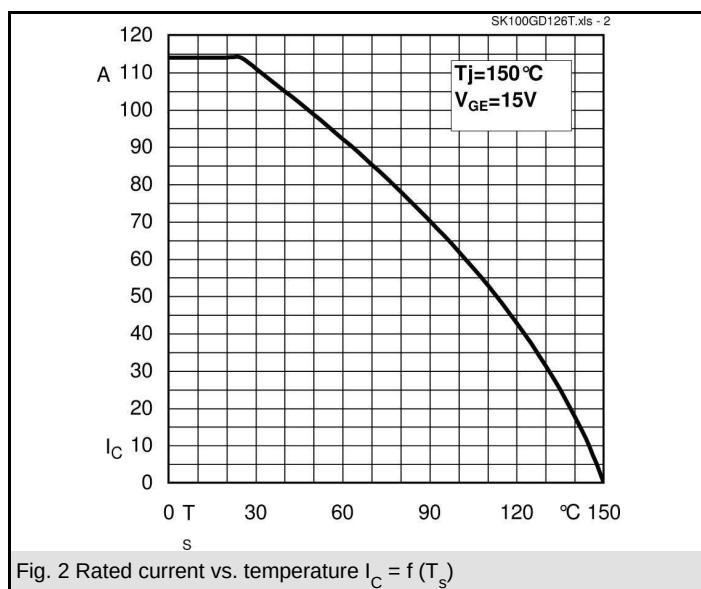
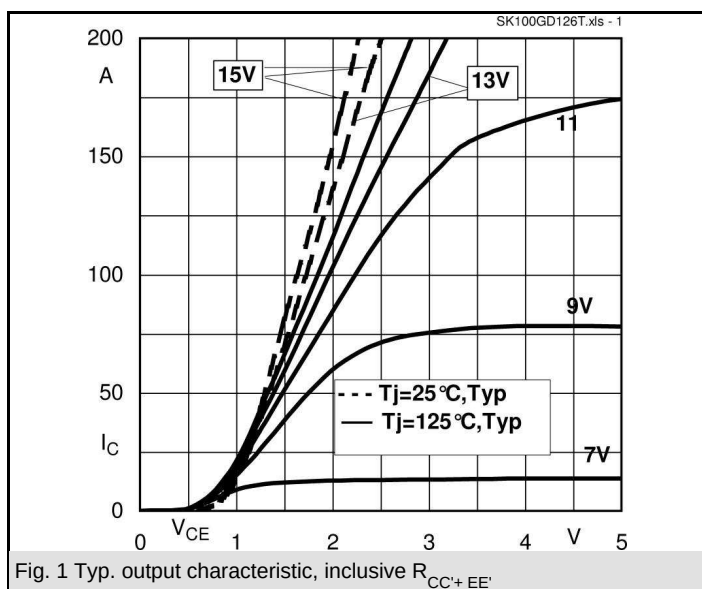
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- Typ. motor power 22 kW

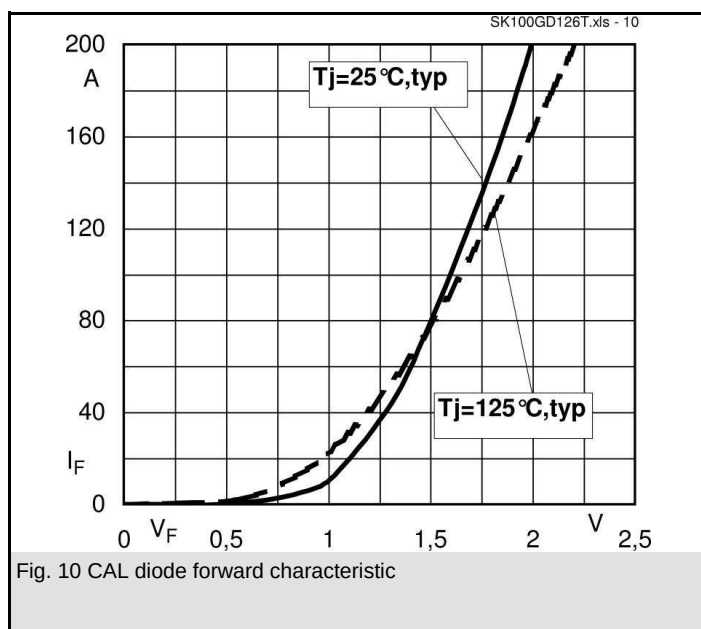
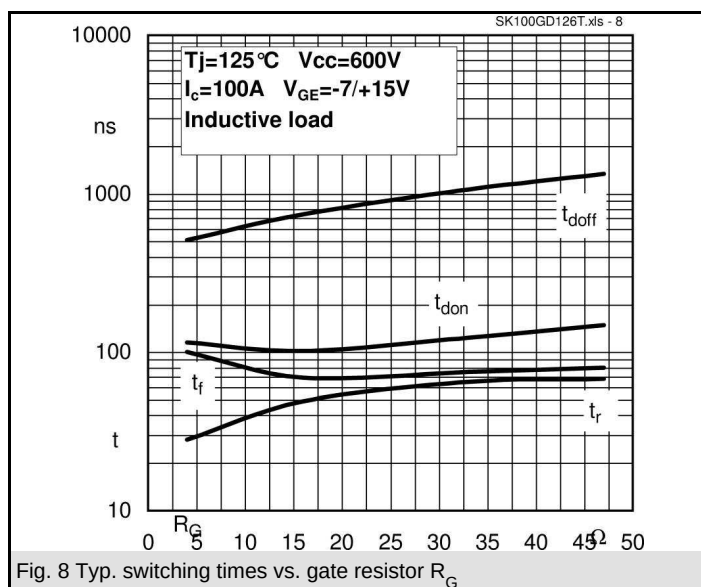
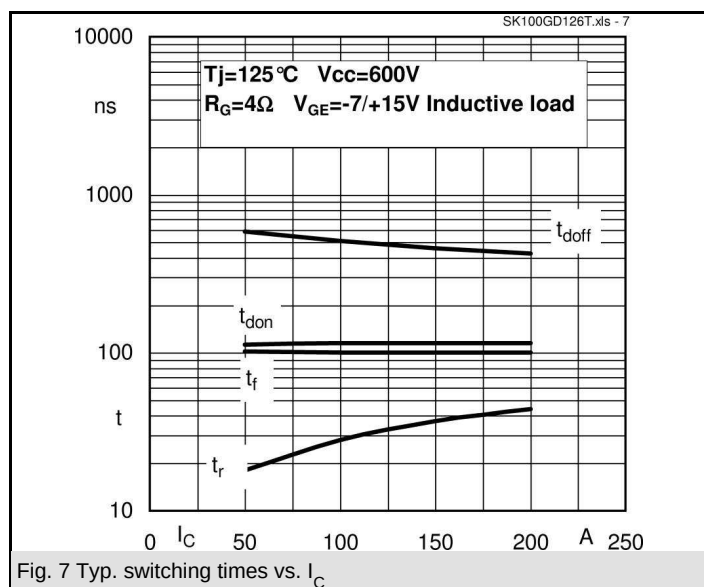


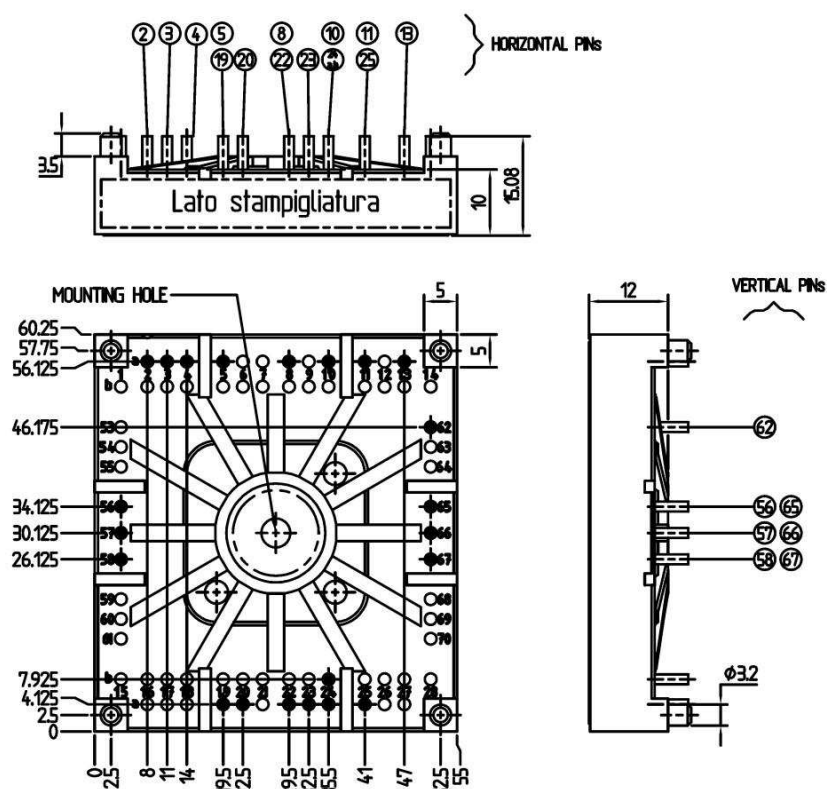
Characteristics		min.	typ.	max.	Units
Symbol	Conditions				
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 100\text{ A}; V_{GE} = 0\text{ V}$				
	$T_j = 25\text{ }^{\circ}\text{C}_{chiplev.}$		1,5		V
	$T_j = 125\text{ }^{\circ}\text{C}_{chiplev.}$		1,5		V
V_{F0}					
	$T_j = 25\text{ }^{\circ}\text{C}$		1,18		V
	$T_j = 125\text{ }^{\circ}\text{C}$		1		V
r_F					
	$T_j = 25\text{ }^{\circ}\text{C}$		3,2		mΩ
	$T_j = 125\text{ }^{\circ}\text{C}$		5		mΩ
I_{RRM}	$I_F = 100\text{ A}$		100		A
Q_{rr}	$di/dt = 2250\text{ A}/\mu\text{s}$		20		μC
E_{rr}	$V_{CC} = 600\text{ V}$		7,3		mJ
$R_{th(j-s)D}$	per diode		0,55		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100\text{ }^{\circ}\text{C} (R_{25} = 5\text{ k}\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

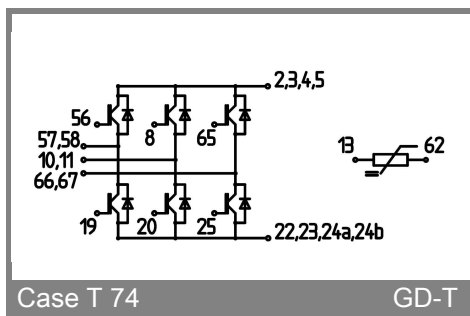
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T